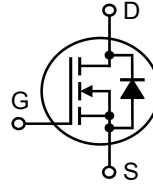


X2-Class HiPerFET™ Power MOSFET

IXFA26N65X2
IXFP26N65X2
IXFH26N65X2

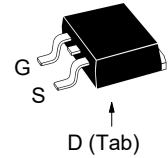
$V_{DSS} = 650V$
 $I_{D25} = 26A$
 $R_{DS(on)} \leq 130m\Omega$

N-Channel Enhancement Mode
Avalanche Rated

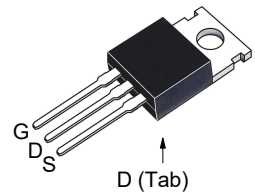


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	650	V
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	650	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ C$	26	A
I_{DM}	$T_C = 25^\circ C$, Pulse Width Limited by T_{JM}	36	A
I_A	$T_C = 25^\circ C$	5	A
E_{AS}	$T_C = 25^\circ C$	1	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$	50	V/ns
P_D	$T_C = 25^\circ C$	460	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb
M_d	Mounting Torque (TO-220 & TO-247)	1.13 / 10	Nm/lb.in
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-247	6.0	g

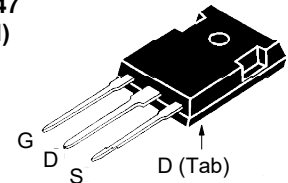
**TO-263
(IXFA)**



**TO-220
(IXFP)**



**TO-247
(IXFH)**



G = Gate D = Drain
S = Source Tab = Drain

Features

- International Standard Packages
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	650		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 2.5mA$	3.5		5.0 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			130 m Ω

Symbol		Test Conditions		Characteristic Values		
		(T _J = 25°C, Unless Otherwise Specified)		Min.	Typ.	Max
g _{fs}	V _{DS} = 20V, I _D = 0.5 • I _{D25} , Note 1	9.5	16.0	S		
R _{Gi}	Gate Input Resistance		0.6	Ω		
C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		2450	pF		
C _{oss}			1360	pF		
C _{rss}			1.2	pF		
Effective Output Capacitance						
C _{o(er)}	Energy related	V _{GS} = 0V V _{DS} = 0.8 • V _{DSS}	90	pF		
C _{o(tr)}	Time related		380	pF		
t _{d(on)}	Resistive Switching Times V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 10Ω (External)		40	ns		
t _r			53	ns		
t _{d(off)}			50	ns		
t _f			17	ns		
Q _{g(on)}	V _{GS} = 10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		45	nC		
Q _{gs}			18	nC		
Q _{gd}			15	nC		
R _{thJC}				0.27 °C/W		
R _{thCS}	TO-220		0.50	°C/W		
	TO-247		0.21	°C/W		

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^{\circ}\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			26 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			104 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 13\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		230	ns
Q_{RM}			1.6	μC
I_{RM}			12	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

Littelfuse reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

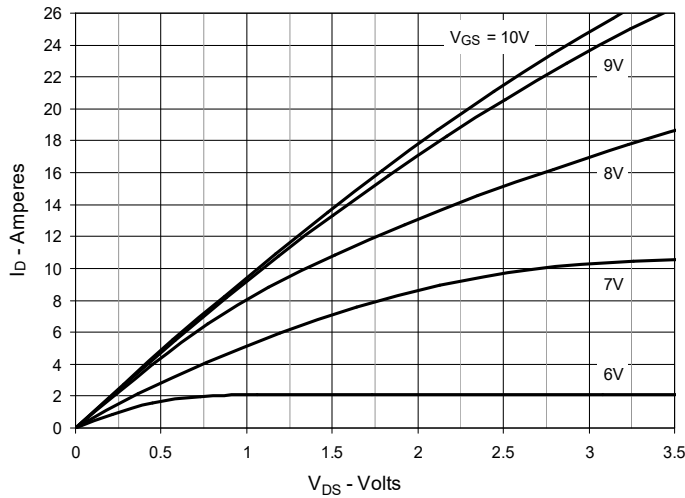


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

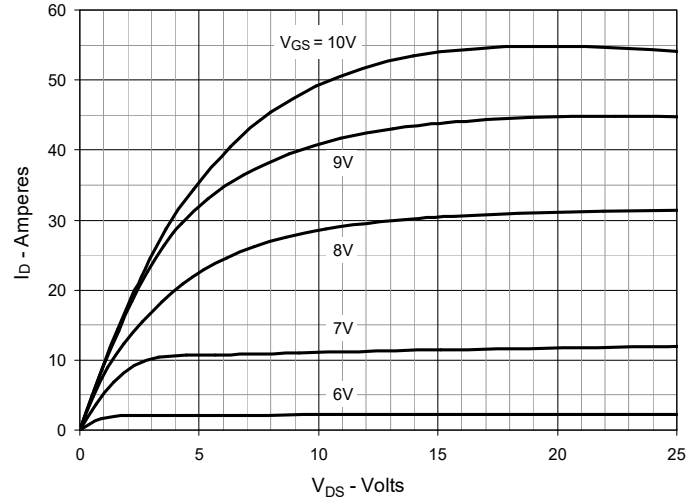


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

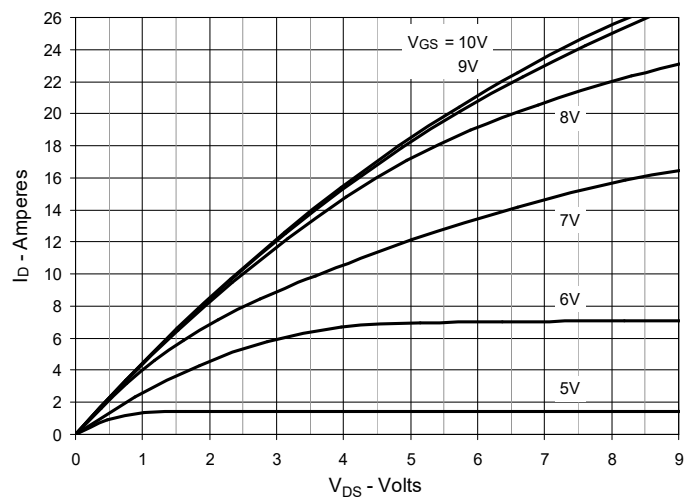


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 13\text{A}$ Value vs. Junction Temperature

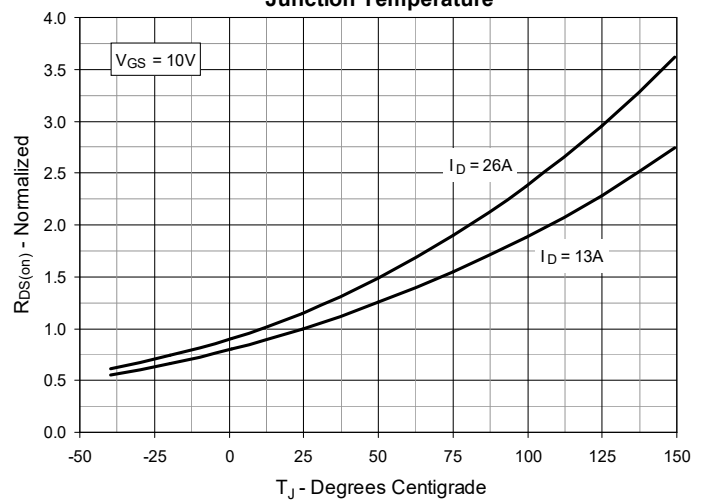


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 13\text{A}$ Value vs. Drain Current

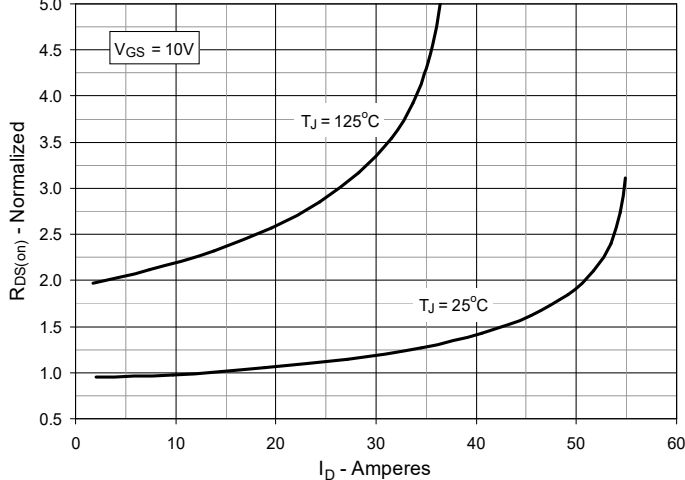


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

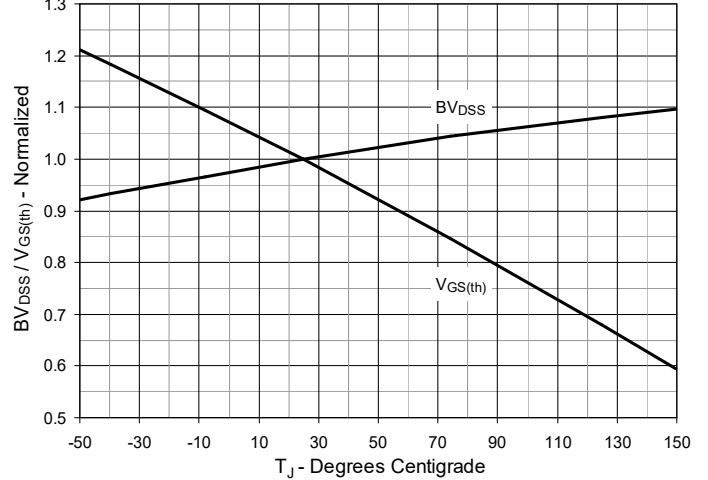


Fig. 7. Maximum Drain Current vs. Case Temperature

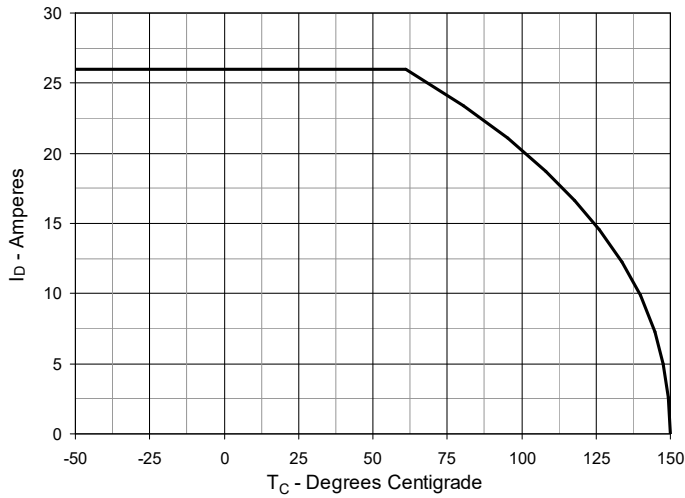


Fig. 8. Input Admittance

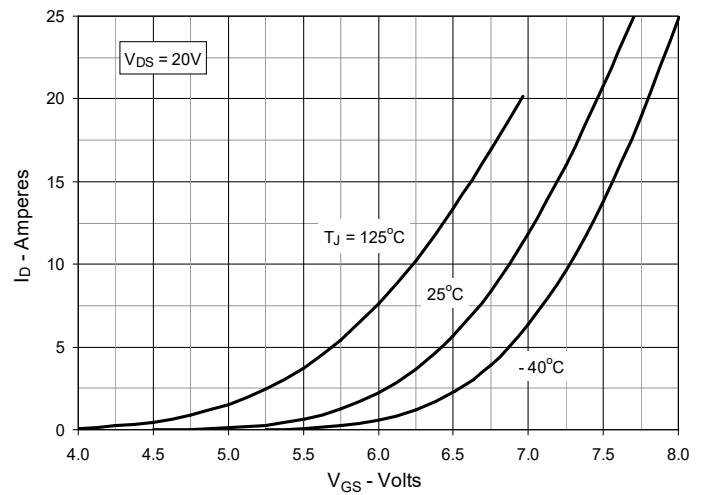


Fig. 9. Transconductance

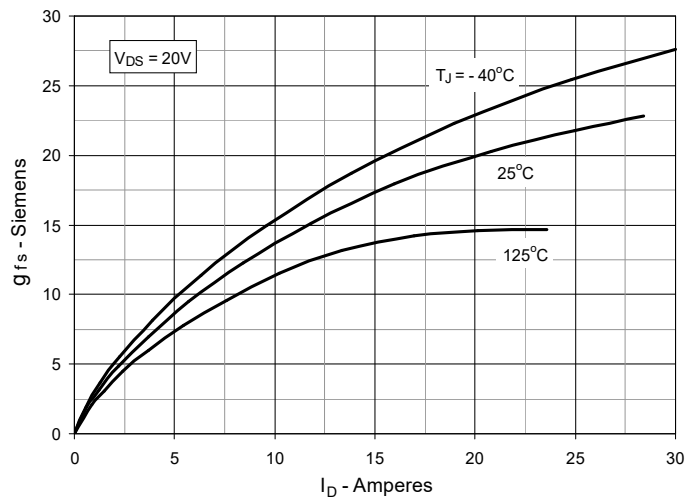


Fig. 10. Forward Voltage Drop of Intrinsic Diode

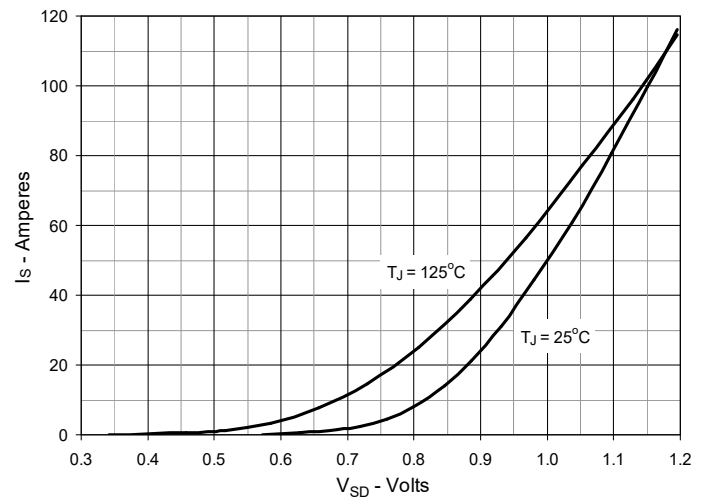


Fig. 11. Gate Charge

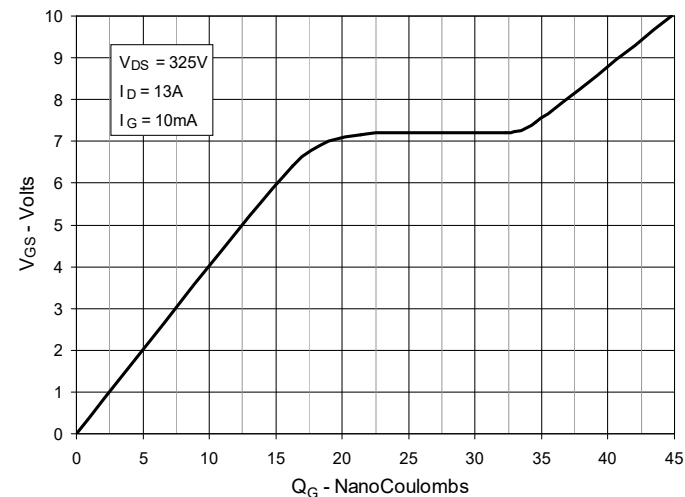


Fig. 12. Capacitance

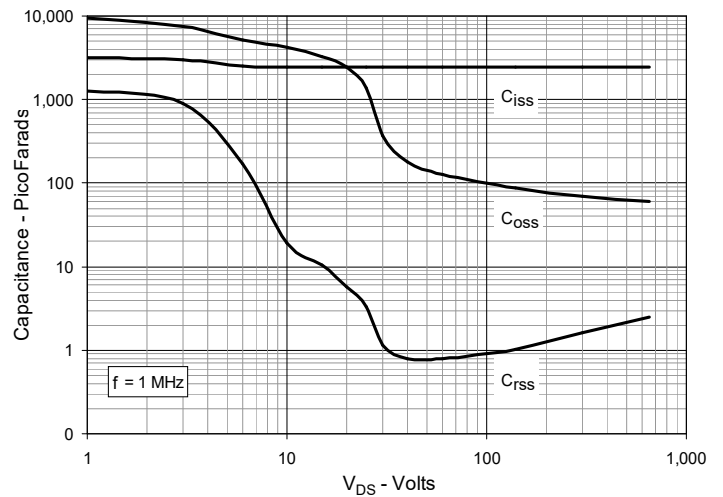


Fig. 13. Output Capacitance Stored Energy

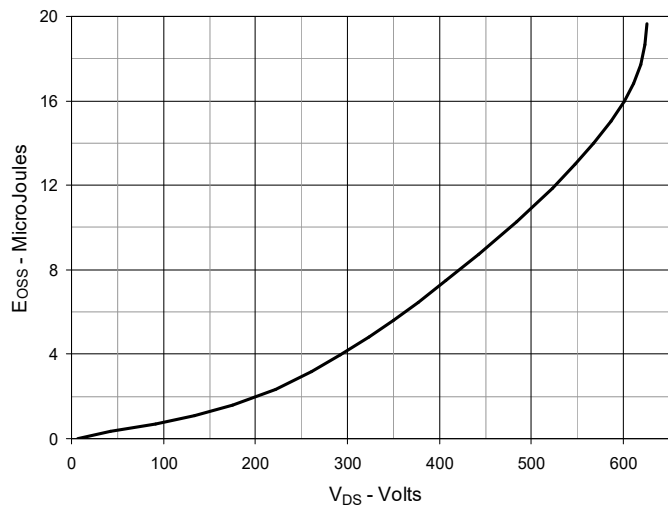


Fig. 14. Forward-Bias Safe Operating Area

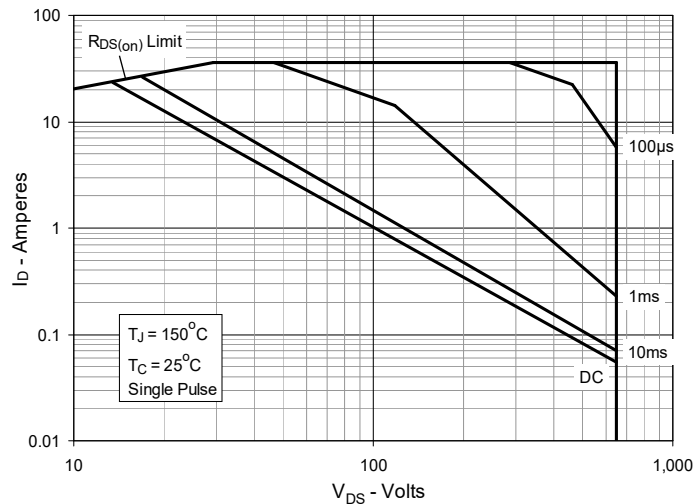
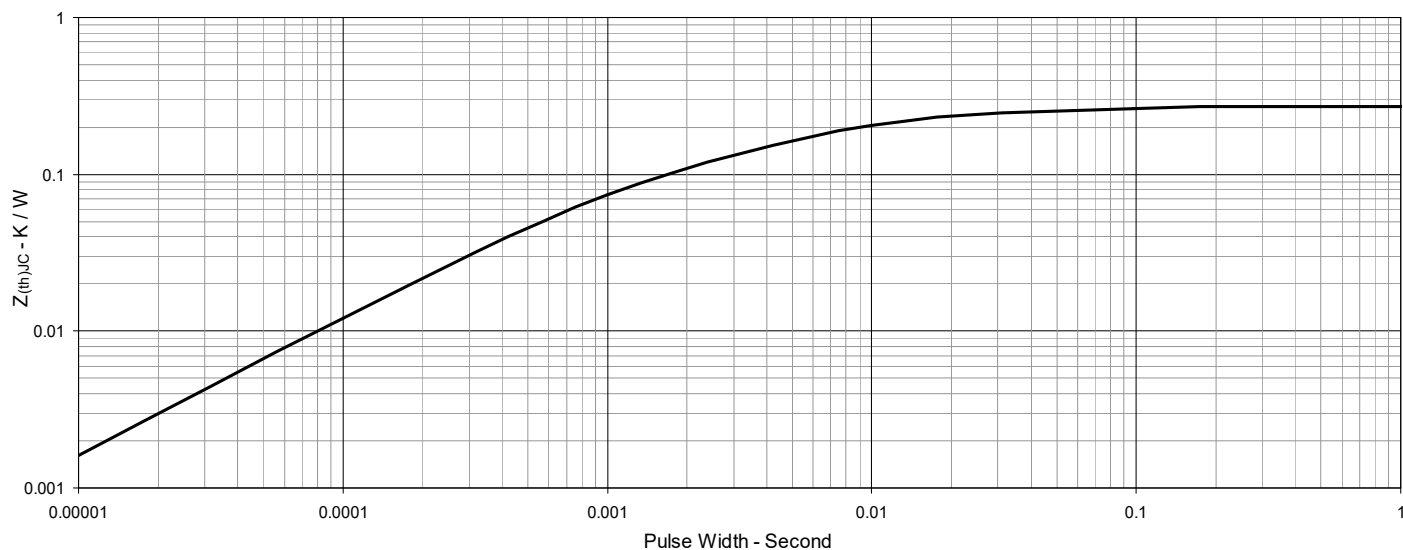
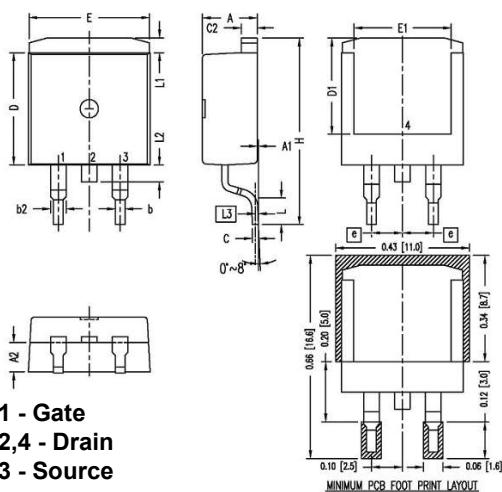


Fig. 15. Maximum Transient Thermal Impedance



TO-263 Outline



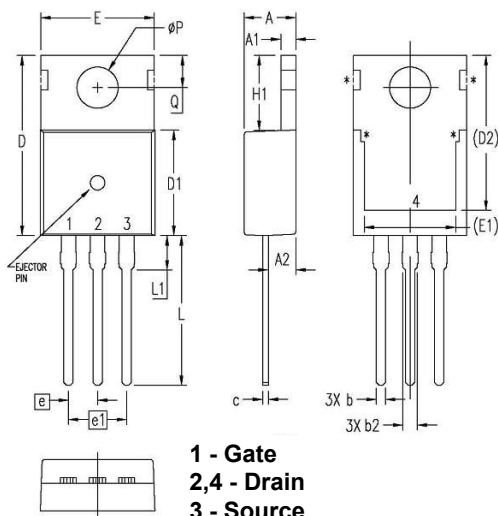
- 1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
(E)	.100	BSC	2.54	BSC
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
IL3	.010	BSC	0.254	BSC

NOTE:

- NOTE:
1. This drawing meets all dimensions requirement of JEDEC outlines TO-263AB.
 2. All metal surface are matte pure tin plated except trimmed area.
 3. ☒ is Gauge plane to measure L.
 4. These dimension do not include mold flash and they will not exceed 0.005[0.13] per side.

TO-220 Outline



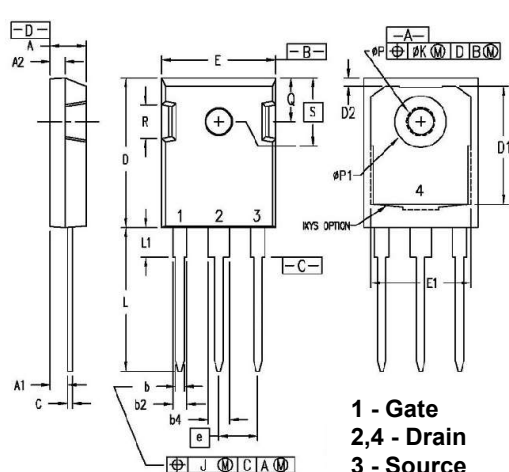
- 1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20

NOTE:

- NOTE:
1. These dimensions do not include mold protrusion.
 2. Metal finish - Matte pure tin plating except trim area.
 3. Pin call out: 1 - GATE 3 - SOURCE (EMITTER for IGBT)
2 - DRAIN (COLLECTOR for IGBT) 4 - DRAIN (Connected with #2 internally)
 4. Ejector pin location & diameter will vary depending on packaging suppliers.
 5. * marked area will vary depending on packaging suppliers.

TO-247 Outline



- 1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
ØP	.140	.144	3.55	3.65
ØP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

NOTE: This drawing will meet all dimensions
requirement of JEDEC outlines TO-247 AD (R-PSIP-F3)

